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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> (use as many sheets as necessary)				Application Number	To Be Assigned
				Filing Date	Herewith
				First Named Inventor	Weiss et al.
				Art Unit	To Be Assigned
				Examiner Name	To Be Assigned
Sheet	1	of	3	Attorney Docket Number	176/61511 (2-11144-03043)

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
JMB	1	US-5,651,818	07/29/1997	Milstein et al.	
JMB	2	US-5,682,401	10/28/1997	Joannopoulos et al.	
JMB	3	US-5,740,287	04/14/1998	Scalora et al.	
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FOREIGN PATENT DOCUMENTS						
Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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JMB	4	Barla et al., "Determination of Lattice Parameter and Elastic Properties of Porous Silicon By X-Ray Diffraction," <i>Growth</i> 68:727-732 (1984)	
JMB	5	Birner et al., "Silicon-Based Photonic Crystals," <i>Adv. Mater.</i> 13:377-389 (2001)	
JMB	6	Striener et al., "Dynamic Etching of Silicon for Broadband Antireflection Applications," <i>Appl. Phys. Lett.</i> 81:2980-2982 (2002)	

Examiner Signature	<i>J. Martin Blin</i>	Date Considered	01/10/2006
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JMB	7	Buttard et al., "X-Ray-Diffraction Investigation of the Anodic Oxidation of Porous Silicon", <i>J. Appl. Phys.</i> 79:8060-8070 (1996)	
JMB	8	Buttard et al., "Porous Silicon Strain During in situ Ultrahigh Vacuum Thermal Annealing," <i>J. Appl. Phys.</i> 85:7105-7111 (1999)	
JMB	9	Yablonovitch et al., "Inhibited Spontaneous Emission in Solid-State Physics and Electronics," <i>Phys. Rev. Lett.</i> 58:2059-2062 (1987)	
JMB	10	Bai et al., "Strain in Porous Si Formed on a Si (100) Substrate," <i>Appl. Phys. Lett.</i> 57:2247-2249 (1990)	
JMB	11	Jellison et al., "The Temperature Dependence of the Refractive Index of Silicon at Elevated Temperatures at Several Laser Wavelengths," <i>J. Appl. Phys.</i> 60:841-843 (1986)	
JMB	12	Martinez, G., in <i>Handbook on Semiconductors Volume 2: Optical Properties of Solids</i> , M. Balkanski, ed. North-Holland Publishing Company, New York, NY, pp. 181-222 (1980)	
JMB	13	Lopez et al., "Erbium Emission from Porous Silicon One-Dimensional Photonic Band Gap Structures," <i>Appl. Phys. Lett.</i> 77:3704-3706 (2000)	
JMB	14	Sugiyama et al., "Microstructure and Lattice Distortion of Anodized Porous Silicon Layers," <i>J. Cryst. Growth</i> 103:156-163 (1990)	
JMB	15	Kim et al., "Effective Method for Stress Reduction in Thick Porous Silicon Films," <i>Appl. Phys. Lett.</i> 80:2287-2289 (2002)	
JMB	16	Lugo et al., "Porous Silicon Multilayer Structures: A Photonic Band Gap Analysis," <i>J. Appl. Phys.</i> 91:4966-4972 (2002)	
JMB	17	Hirschman et al., "Silicon-Based Visible Light-Emitting Devices Integrated Into Microelectric Circuits," <i>Nature</i> 384:338-341 (1996)	
JMB	18	Young et al., "X-Ray Double Crystal Diffraction Study of Porous Silicon," <i>Appl. Phys. Lett.</i> 46:1133-1135 (1985)	

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JMB	19	Savage, N., "Linking with Light," <i>IEEE Spectrum</i> 39:32-36 (2002)	
JMB	20	Painter et al., "Two-Dimensional Photonic Band-Gap Defect Mode Laser," <i>Science</i> 284:1819-1821 (1999)	
JMB	21	Reece et al., "Optical Microactivities with Subnanometer Linewidths Based on Porous Silicon," <i>Appl. Phys. Lett.</i> 81:4895-4897 (2002)	
JMB	22	Lee et al., "Operation of Photonic Crystal Membrane Lasers Above Room Temperature," <i>Appl. Phys. Lett.</i> 81:3311-3313 (2002)	
JMB	23	John, S., "Strong Localization of Photons in Certain Disordered Dielectric Superlattices," <i>Phys. Rev. Lett.</i> 58:2486-2489 (1987)	
JMB	24	Weiss et al., "Electrically Tunable Silicon-Based Mirrors," <i>Proc. of SPIE</i> 4654:36-44 (2002)	
JMB	25	Lin et al., "Demonstration of Highly Efficient Waveguiding in a Photonic Crystal Slab at the 1.5- $\mu$ m Wavelength," <i>Opt. Lett.</i> 25:1297-1299 (2000)	
JMB	26	Theiß, W., "Optical Properties of Porous Silicon," <i>Surf. Sci. Rep.</i> 29:91-192 (1997)	
JMB	27	Zhou et al., "The Effect of Thermal Processing on Multilayer Porous Silicon Microactivity," <i>Phys. Stat. Sol. A</i> 182:319-324 (2000)	
JMB	28	Weiss et al., "Temperature Stability for Silicon-Based Photonic Band-Gap Structures," <i>Applied Physics Letters</i> 83:1980-1982 (2003)	
JMB	29	DeLouise, Lisa, [http://www.futurehealth.rochester.edu/miller_group/people/lisa_delouise.html] Miller Research Group pp. 1-4 (2004)	
JMB	30	S.M. Weiss, "Control of One-Dimensional Photonic Bandgap Thermal Tuning," <i>Phys. Stat. Sol.</i> pp. 1-5 (Unpublished)	
JMB	31	Grayson, M., ed., <i>Encyclopedia of Semiconductor Technology</i> , John Wiley and Sons, New York, pp. 374 (1984)	

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